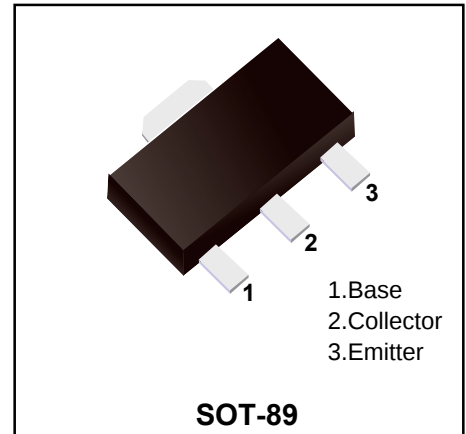


Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

- ◆Compliment to 2N3904SI
- ◆Low current
- ◆Low voltage



Marking Code

2N3906SI

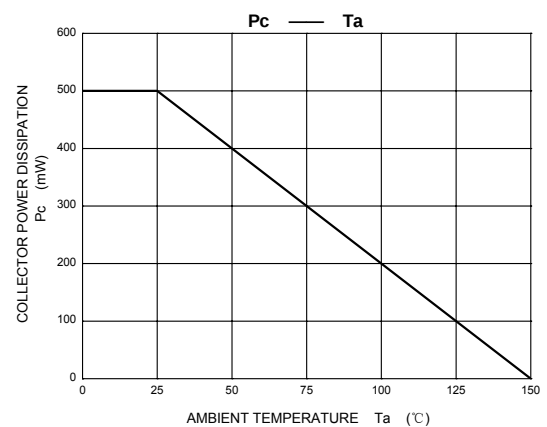
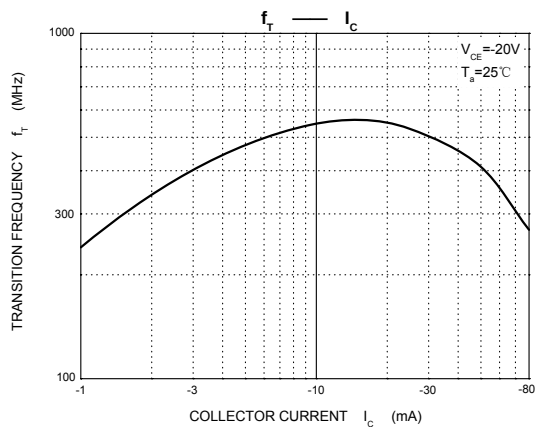
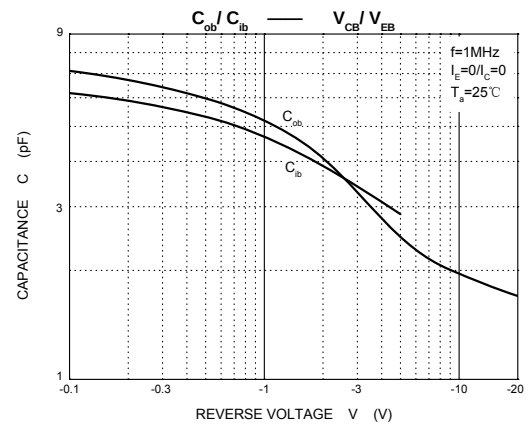
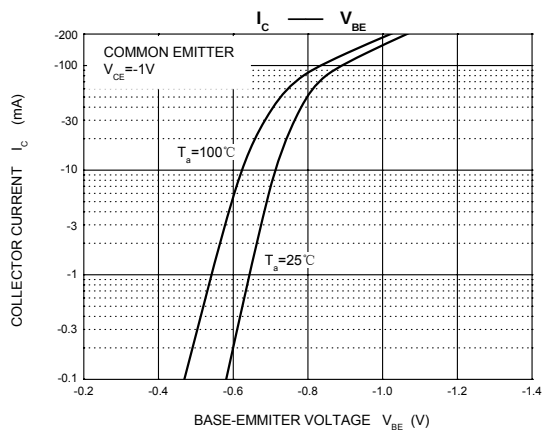
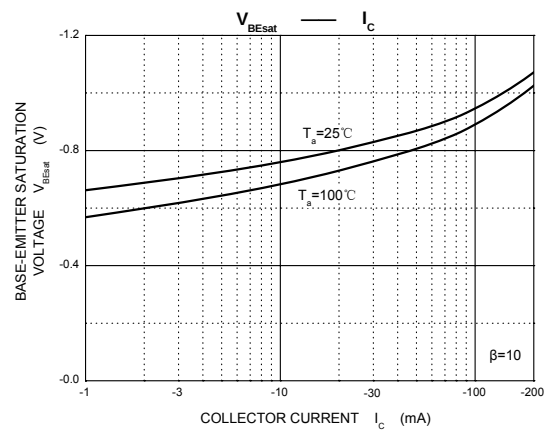
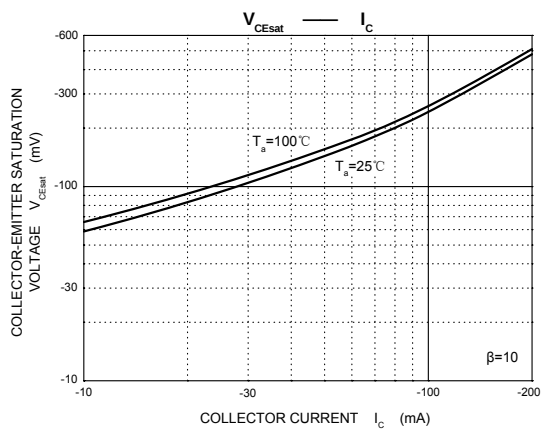
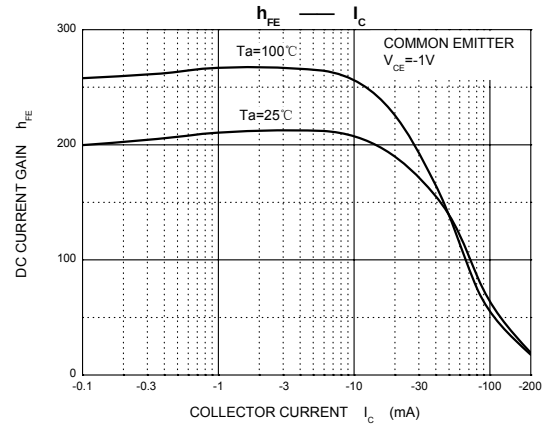
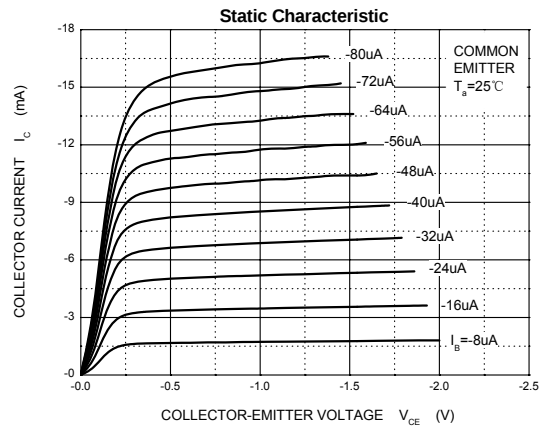
2A

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-0.2	A
P_C	Collector Power Dissipation	0.5	W
R_{JA}	Thermal resistance from junction to ambient	250	°C/W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-0.05	μA
Collector ut-off current	I_{CEX}	$V_{CB} = -30V, V_{BE(off)} = -3V$			-0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -0.1mA$	60			
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -1mA$	80			
	$h_{FE(3)}$	$V_{CE} = -1V, I_C = -10mA$	100		300	
	$h_{FE(4)}$	$V_{CE} = -1V, I_C = -50mA$	60			
	$h_{FE(5)}$	$V_{CE} = -1V, I_C = -100mA$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = -10mA, I_B = -1mA$			-0.25	V
	$V_{CE(sat)2}$	$I_C = -50mA, I_B = -5mA$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C = -10mA, I_B = -1mA$	-0.65		-0.85	V
	$V_{BE(sat)2}$	$I_C = -50mA, I_B = -5mA$			-0.95	V
Transition frequency	f_T	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$	250			MHz
Collector capacitance	C_c	$V_{CB} = -5V, I_E = 0, f = 1MHz$			4.5	pF
Emitter capacitance	C_e	$V_{EB} = -0.5V, I_C = 0, f = 1MHz$			10	pF
Noise figure	NF	$V_{CE} = -5V, I_C = -0.1mA, f = 10Hz-15.7kHz, R_S = 1K\Omega$			4	dB
Delay time	t_d	$I_C = -10mA, I_{B1} = -I_{B2} = -1mA$			35	nS
Rise time	t_r				35	nS
Storage time	t_s				225	nS
Fall time	t_f				75	nS



Ordering information

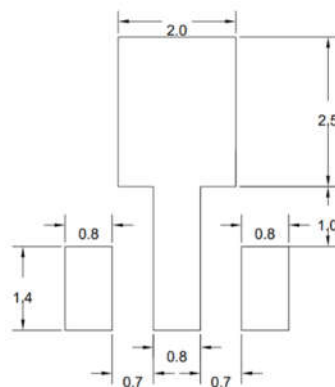
Package	Packing Description	Base Quantity	Packing Quantity
SOT-89	Tape/Reel, 7" reel	3000pcs/Reel	30000PCS/Carton

Package Dimensions

SOT-89

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	1.40	1.60	0.055	0.063
b	0.32	0.52	0.013	0.020
b1	0.38	0.58	0.015	0.023
c	0.35	0.45	0.014	0.018
D	4.40	4.60	0.173	0.181
D1	1.45	1.65	0.057	0.065
D2	1.70	1.80	0.067	0.071
E	2.30	2.60	0.091	0.102
E1	3.95	4.25	0.156	0.167
E2	1.80	2.00	0.071	0.079
e	1.40	1.60	0.055	0.063
e1	2.80	3.20	0.110	0.126
L	0.90	1.20	0.035	0.047

The recommended mounting pad size



UNIT:MM

Disclaimer

The information presented in this document is for reference only. Guangdong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <https://www.yfwdiode.com>, or consult YFW sales office for further assistance.